K. Memory (Design & Process Technology) 분과
[TG1-K] Devices for Neuromorphic Computing I

TG1-K-1 09:00~09:30	**[초청]** **On-Chip Trainable Analog Phase Change Memory (PCM) Synaptic Array for Spiking Restricted Boltzmann Machine (RBM)** SangBum Kim *Department of Materials Science and Engineering, Seoul National University*
TG1-K-2 09:30~09:45	**Synaptic Device Failure Analysis of Array-Based Neuromorphic System Using Sigmoidal TS Neuron** Wooseok Choi, Donguk Lee, and Hyunsang Hwang *Center for Single Atom-based Semiconductor Device and the Department of MS&E, POSTECH*
TG1-K-3 09:45~10:00	**Influence of Al_2O_3 Insertion Layer on RS/Retention Characteristics in IGZO Memristor for Neuromorphic Application** Woo Sik Choi, Jun Tae Jang, Jungi Min, Donguk Kim, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim *School of Electrical Engineering, Kookmin University*
TG1-K-4 10:00~10:15	**Training and Operation of an Artificial Neural Network in IGZO-based Crossbar Array** Jun Tae Jang, Jungi Min, Woo Sik Choi, Donguk Kim, Jingyu Park, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim *School of Electrical Engineering, Kookmin University*
TG1-K-5 10:15~10:30	**MOSFET Compensated Synapse Device for Analog Neuromorphic System** Chuljun Lee, Myungjun Kim, Yubin Song, and Daeseok Lee *Department of Electronic Materials Engineering, Kwangwoon University*